

IN THE SPECIFICATION

Please replace the first full paragraph of page 8 with the following:

A1
Fig. 2 illustrates the silicon implantation pre-treatment of the present invention. Silicon ions are implanted 20 into the low-k material layer at an energy of between about 5 and 30 KeV with a dosage of between about $1 \text{ E } 12$ and $1 \text{ E } 16$ ions/cm². The targeted mean depth of implantation is between about 50 and 600 Angstroms. Fig. 3 illustrates the roughened silicon-implanted surface 21 of the low-k material layer 18.

IN THE CLAIMS

Please amend the Claims as follows:

A2
1. (AMENDED) A method of forming a dielectric material layer comprising:

depositing a low dielectric constant material layer on a substrate wherein said low dielectric constant
5 material comprises: porous or non-porous carbon-based silicon oxides, porous or non-porous doped silicon oxides, porous or non-porous organic polymers, or porous